CS-01-111

January 5, 2004

To: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject: Serial No. 10/676,896 10/01/03

Vincent Ho et al.

PROCESS TO MANUFACTURE NONVOLATILE MOS MEMORY DEVICE

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on January 27, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date 1/27/04

"A Silicon Nanocrystals Based Memory," Tiwari et al., Appl. Phys. Lett. 68(10), March 4, 1996, pp. 1377-1379, demonstrates quasi-nonvolatile MOS memory devices employing silicon nanocrystal charge-storage sites produced by ion implantation into the gate oxide.

Ya-Chin King et al., "MOS Memory Using Germanium Nanocrystals Formed by Thermal Oxidation of Si1-xGex," IEDM Tech. Digest, 1998, pp. 115-118, discloses a novel technique of fabricating germanium nanocrystal quasi-nonvolatile memory device.

CS-01-074, Serial No. 10/087,506, Filed March 1, 2002, now issued as U.S. Patent 6,656,792, "Nanocrystal Flash Memory Device and Manufacturing Method Therefor," asigned to a common assignee, discusses using radio-frequency co-sputtering and rapid thermal annealing to form the oxide layer containing germanium nanocrystals.

U.S. Patent 6,128,243 to Chan et al., "Shadow Memory for a SRAM and Method," discloses a memory for a SRAM using germanium Nanocrystals.

U.S. Patent 5,783,498 to Dotta, "Method of Forming Silicon Dioxide Film Containing Germanium Nonocrystals," discloses a process to form germanium Nonocrystals.

U.S. Patent 6,060,743 to Sugiyama et al., "Semiconductor Memory Device Having Multilayer Group IV Nanocrystal Quantum Dot Floating Gate and Method of Manufacturing the Same," discloses a memory device using germanium Nanocrystals.

U.S. Patent 6,090,666 to Ueda et al., "Method for Fabricating Semiconductor Nanocrystal and Semiconductor Memory Device Using the Semiconductor Nanocrystal," discloses a memory device using germanium Nanocrystals.

Sincerely,

Stephen B. Ackerman,
Reg. No. 37761

Form PTO-1449

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several sheets if necessary)

Docket Number (Optional)	Application Number
CS-01-111	10/676,896
Applicant: Vincent Ho et al.	
Filing Date: 10/01/03	Group Art Unit

U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	6128243	10/3/00	Cham et al.	365	227	12/3/99
	5783498	7/21/98	Dotta	438	778	5/28/96
	6060743	5/9/00	Sugiyama et al.	257	321	5/20/98
	6090666	7/18/00	Ueda et al.	438	257	9/30/98
	6656792	12/2/03	Choi et al.	438	257	3/1/02

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES	Translation NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

- Ya-Chin King et al., "MOS Memory Using Germanium Nanocrystals Formed by Thermal Oxidation of $Si_{1-x}Ge_x$," IEDM Tech. Digest, 1998, pp. 115-118.
- "A Silicon Nanocrystals Based Memory", Tiwari et al., Appl. Phys. Lett. 68(10), pp. 1377-1379, March 4, 1996.

EXAMINER	DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.